NAF

Docket No.: 14467.05

· IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

First Named

John P. Snyder

Inventor:

Application

10/796,514

No.:

Filing Date:

03/09/2004

NOV 1 5 7007 W

Confirmation No.:

1961

Examiner:

Kim, Su C

Group Art Unit:

2823

Title:

TRANSISTOR HAVING HIGH DIELECTRIC

GATE INSULATING LAYER AND SOURCE

AND DRAIN FORMING SCHOTTKY CONTACT WITH SUBSTRATE

TRANSMITTAL LETTER

Mail Stop AF Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450 I hereby certify that this document is being sent via First Class U.S. mail addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 3 day of Avenue; 2007.

DOTZ

(Signature)

Dear Sir:

The following documents are enclosed in connection with the above-referenced patent application:

- 1. Response After Final (14 pages);
- 2. Petition for Extension of Period for Response (1 page);
- 3. Credit Card Payment Form in the amount of \$230 to cover the two-month extension of time fee (1 page); and
- 4. Return Receipt Postcard

Respectfully submitted,

Date: 11/13/2007

3v: (/) ______

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